



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/146,851	09/03/1998	MARK MCQUEEN	3522US(97-10	9940

7590 12/19/2002
JOSEPH A. WALKOWSKI
TRASK BRITT & ROSSA
POST OFFICE BOX 2550
SALT LAKE CITY, UT 84110

EXAMINER

FENTY, JESSE A

ART UNIT	PAPER NUMBER
----------	--------------

2815

DATE MAILED: 12/19/2002

30

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/146,851

Applicant(s)

MCQUEEN, MARK

Examiner

Jesse A. Fenty

Art Unit

2815

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 19 September 2002.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1,3-6,9,10,19,21-24,27 and 28 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1,3-6,9,10,19,21-24,27 and 28 is/are rejected.--
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☒ The proposed drawing correction filed on 19 September 2002 is: a) ☒ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____
- 4) ☐ Interview Summary (PTO-413) Paper No(s) _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 1, 3-6, 9, 10, 19, 21-24, 27 and 28 are rejected under 35 U.S.C. 103(a) as being unpatentable over Watanabe (U.S. Patent No. 6,124,189) in view of Huang et al. (U.S. Patent No. 6,084,304).

In re claim 1 and 19, Watanabe (Figs. 7A-7C) discloses a semiconductor device comprising:

A single contact plug (11c) extending through a first barrier layer (108) planarized down to a transistor gate member, said single contact plug in electrical communication with an active region (107) of a semiconductor substrate (100); and

An individual contact land (114) disposed atop said single contact plug and a portion of said first barrier layer, wherein said contact land is wider than said single contact plug and is substantially planar.

Watanabe does not expressly disclose an upper contact extending through a second barrier layer, said second barrier layer disposed over said first barrier layer, to form an electrical contact with said individual contact land. Joshi et al. (Fig. 6) discloses an upper contact (248) extending through a second barrier layer (246), to form an electrical contact with a lower, wider contact

Art Unit: 2815

land (242). It would have been obvious for one skilled in the art at the time of the invention to improve upon the device of Watanabe in the manner of a more comprehensive interconnect structure as disclosed by Joshi for the purpose, for example, of providing a multi-level interconnect structure that will provide greater device insulation of the device active region yet provide the desired conductivity of Joshi to upper level devices.

In re claims 3 and 21, Watanabe (Figs. 7A-7C) discloses a semiconductor device, comprising:

An intermediate structure comprising a substrate having at least one active area including at least one implanted drain region (107), and at least one implanted source region (107a), said intermediate structure further including at least one transistor gate member (130) spanned between said at least one drain region and said at least one source region on said at least one active area;

A first barrier layer (108) planarized down to said at least one transistor gate member, said at least one active area and adjacent said at least one transistor gate member;

At least one drain contact plug (111C) extending through said first barrier layer, wherein said at least one drain contact plug is in electrical communication with said at least one drain region on said substrate;

At least one source contact plug (same) extending through said first barrier layer, wherein said at least one source contact plug is in electrical communication with said at least one source region on said substrate;

Art Unit: 2815

An individual drain contact land (114) disposed atop each of said at least one drain contact plugs and a portion of said first barrier layer, said individual drain contact land wider than said at least one drain contact plug and substantially planar; and

An individual source contact land (same) disposed atop each of said at least one source contact plugs and a portion of said first barrier layer, said individual source contact land wider than said at least one source contact plug and substantially planar.

Watanabe does not expressly disclose a second barrier layer with second source and drain contacts extending through said second barrier layer to establish communication with the source and drain contact lands. Joshi et al. (Fig. 6) discloses an upper contact (248) extending through a second barrier layer (246), to form an electrical contact with a lower, wider contact land (242). It would have been obvious for one skilled in the art at the time of the invention to improve upon the device of Watanabe in the manner of a more comprehensive interconnect structure as disclosed by Joshi for the purpose, for example, of providing a multi-level interconnect structure that will provide greater device insulation of the device active region yet provide the desired conductivity of Joshi to upper level devices.

Watanabe does not expressly disclose a field oxide layer. Joshi (Fig. 6) disclose such a layer (222). It would have been obvious to one skilled in the art at the time of the invention to use a field oxide layer in the device of Pan for the well known purpose of isolating one device from another in a semiconductor substrate, similarly referred to by Joshi as shallow trench isolation (Joshi; column 7, lines 41-43).

In re claims 4 and 22, Watanabe in view of Joshi disclose the devices of claims 3 and 21 respectively, further comprising drain contact metallization (upper 248) in electrical

Art Unit: 2815

communication with said at least one upper drain contact; and source contact metallization (upper 248) in electrical communication with said at least one upper source contact.

In re claims 5 and 23, Watanabe in view of Joshi disclose the devices of claims 3 and 21 respectively, wherein said at least one source contact plug extends between at least two source regions.

In re claims 6 and 24, Watanabe in view of Joshi disclose the devices of claims 3 and 21 respectively, wherein said at least one drain contact plug extends between at least two drain regions.

In re claims 9 and 27, Watanabe in view of Joshi disclose the devices of claims 3 and 21 respectively, wherein said at least one upper source contact extends between at least two individual source contact lands.

In re claims 10 and 28, Watanabe in view of Joshi disclose the devices of claims 3 and 21 respectively, wherein said at least one upper drain contact extends between at least two individual drain contact lands.

Response to Arguments

3. Applicant's arguments with regard to the Office Action mailed 06/19/02 were persuasive. Applicant correctly pointed out that the contact lands of the Pan reference as relied upon by the Examiner were not "disposed atop the barrier layer" as claimed. Accordingly, the rejection based on the Pan prior art is rescinded and a new rejection is presented comprising prior art that reads on the claims of the instant application.

Art Unit: 2815

4. Applicant's further arguments with respect to claims 1, 3-6, 9, 10, 19, 21-24, 27 and 28 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

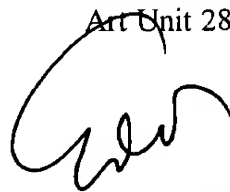
Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jesse A. Fenty whose telephone number is 703-308-8137. The examiner can normally be reached on 5/4-9 1st Fri. Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie Lee can be reached on 703-308-1690. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-746-3892 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Jesse A. Fenty
Examiner
Art Unit 2815

JAF
December 15, 2002



EDDIE LEE
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800